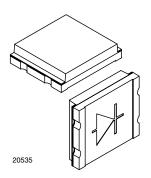


DESCRIPTION

Vishay Semiconductors

Silicon PIN Photodiode

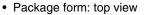


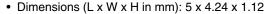
TEMD5080X01 is a PIN photodiode with enhanced blue

sensitivity. The miniature surface mount package (SMD) include a chip with 7.7 mm² sensitive area, covered by clear

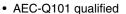
FEATURES

• Package type: surface mount





• Radiant sensitive area (in mm²): 7.7



 Enhanced blue photo sensitivity: S (400 nm) rel > 30 %



- · Peak sensitivity at 940 nm
- · Suitable for visible and near infrared radiation
- Low junction capacitance
- · Fast response times
- Angle of half sensitivity: $\varphi = \pm 65^{\circ}$
- Floor life: 72 h, MSL 4, acc. J-STD-020
- · Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications

APPLICATIONS

· High speed photo detector

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.1} (nm)	
TEMD5080X01	60	± 65	350 to 1100	

Note

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Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TEMD5080X01	Tape and reel	MOQ: 1500 pcs, 1500 pcs/reel	Top view		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	25	V	
Power dissipation	T _{amb} ≤ 25 °C	P _V	215	mW	
Junction temperature		T _j	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 110	°C	
Soldering temperature	Acc. reflow solder profile fig. 8	T _{sd}	260	°C	
Thermal resistance junction/ambient		R _{thJA}	350	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

Vishay Semiconductors

Silicon PIN Photodiode



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	25			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	10	nA
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _D		90		pF
	V _R = 3 V, f = 1 MHz, E = 0	C _D		30	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I _k		50		μΑ
Temperature coefficient of I _k	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{Ik}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \ \lambda = 400 \text{ nm},$ $V_R = 5 \text{ V}$	I _{ra}		18		μΑ
	$E_V = 100 \text{ lx, CIE illuminant A,}$ $V_R = 5 \text{ V}$	I _{ra}		8.5		μΑ
	$E_e = 1 \text{ mW/cm}^2, \ \lambda = 950 \text{ nm}, \ V_R = 5 \text{ V}$	I _{ra}		60		μΑ
Temperature coefficient of I _{ra}	CIE illuminant A	TK _{Ira}		0.15		%/K
	$\lambda = 950 \text{ nm}$	TK _{Ira}		0.1		%/K
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λ_{p}		940		nm
Range of spectral bandwidth		λ _{0.1}		350 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 400 \text{ nm}$	NEP		1.1 x 10 ⁻¹³		W/√Hz
Rise time	$V_R = 5 \text{ V}, R_L = 50 \Omega,$ $\lambda = 850 \text{ nm}$	t _r		40		ns
Fall time	$V_R = 5 \text{ V}, R_L = 50 \Omega,$ $\lambda = 850 \text{ nm}$	t _f		40		ns

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

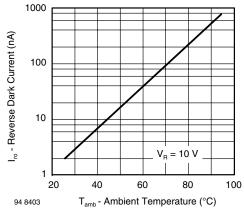


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

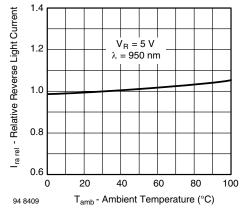


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



Silicon PIN Photodiode

Vishay Semiconductors

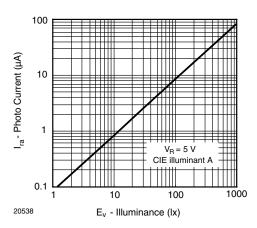


Fig. 3 - Reverse Light Current vs. Irradiance

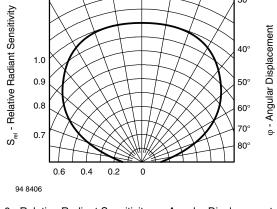


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

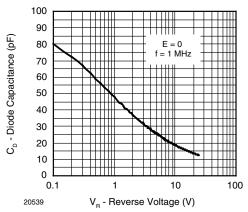


Fig. 4 - Diode Capacitance vs. Reverse Voltage

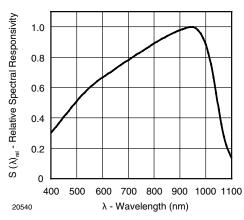


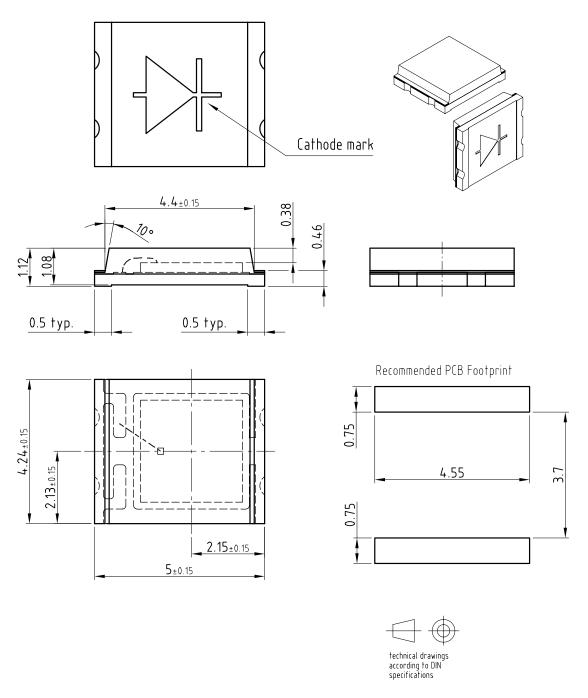
Fig. 5 - Relative Spectral Sensitivity vs. Wavelength

Vishay Semiconductors

Silicon PIN Photodiode



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.541-5060.01-4

Issue: 3; 05.02.08

20536

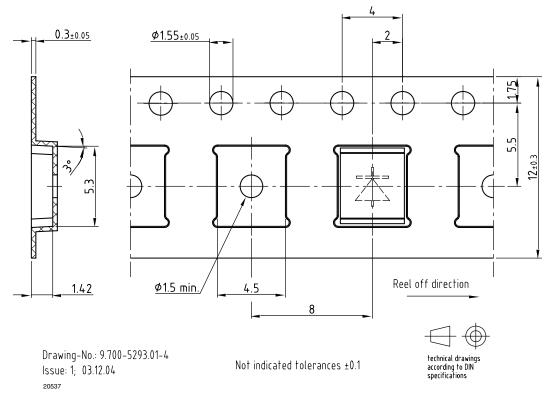
Not indicated tolerances ± 0.1



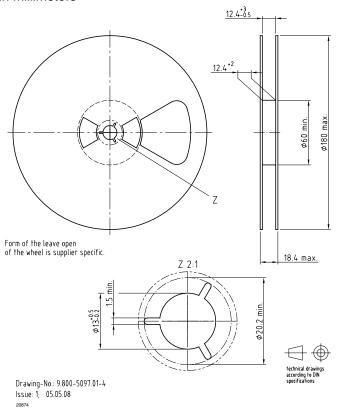
Silicon PIN Photodiode

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TAPING DIMENSIONS in millimeters



REEL DIMENSIONS in millimeters



Silicon PIN Photodiode



SOLDER PROFILE

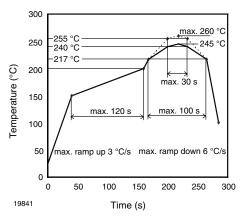


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 4

Floor life: 72 h

Conditions: T_{amb} < 30 °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at 40 °C (+ 5 °C), RH < 5 %

or

96 h at 60 °C (+ 5 °C), RH < 5 %.





Vishay

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